

# PolarHV™ HiPerFET IXFH 140N10P Power MOSFETs IXFT 140N10P

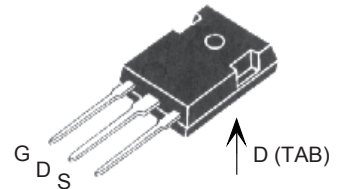
N-Channel Enhancement Mode  
Fast Intrinsic Diode  
Avalanche Rated



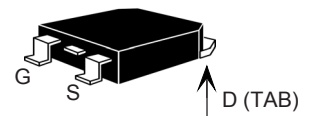
$$\begin{aligned} V_{DSS} &= 100 \text{ V} \\ I_{D25} &= 140 \text{ A} \\ R_{DS(on)} &\leq 11 \text{ m}\Omega \\ t_{rr} &\leq 150 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	100	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	100	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	140	A
$I_{D(RMS)}$	External lead current limit	75	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	300	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	60	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	80	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	2.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 4 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	600	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10s	260	$^\circ\text{C}$
$M_d$	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6.0	g
	TO-268	5.0	g

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate      D = Drain  
S = Source      TAB = Drain

## Features

- † International standard packages
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

## Advantages

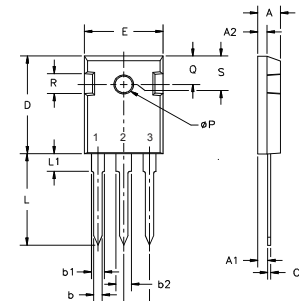
- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4.0 \text{ mA}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 175^\circ\text{C}$			25 $\mu\text{A}$
				500 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ $V_{GS} = 15 \text{ V}$ , $I_D = 300 \text{ A}$ Note 1	9		11 $\text{m}\Omega$ m $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = 0.5 I_{D25}$ , Note 1	45	65	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		4700	pF
$C_{oss}$			1850	pF
$C_{rss}$			600	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 60\text{ A}$ $R_G = 4\ \Omega$ (External)		35	ns
$t_r$			50	ns
$t_{d(off)}$			85	ns
$t_f$			26	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$		155	nC
$Q_{gs}$			33	nC
$Q_{gd}$			85	nC
$R_{thJC}$	(TO-247)			$0.25^\circ\text{C/W}$
$R_{thCS}$		0.21		$^\circ\text{C/W}$

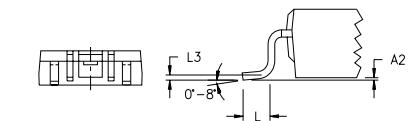
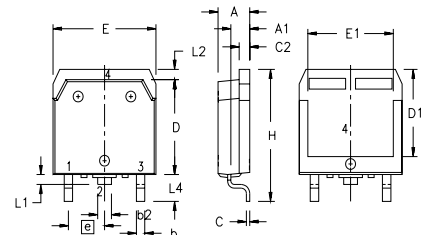
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			140 A
$I_{SM}$	Repetitive			300 A
$V_{SD}$	$I_F = I_s$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 50\text{ V}$ , $V_{GS} = 0\text{ V}$		150	200 ns
$Q_{RM}$			0.8	$\mu\text{C}$
$I_{RM}$			6	A

Note 1: Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$

**TO-247 AD Outline**


Terminals: 1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-268 Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010 BSC		0.25 BSC	
L <sub>4</sub>	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

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 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

**Fig. 1. Output Characteristics**  
**@ 25°C**



**Fig. 2. Extended Output Characteristics**  
**@ 25°C**



**Fig. 3. Output Characteristics**  
**@ 150°C**



**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



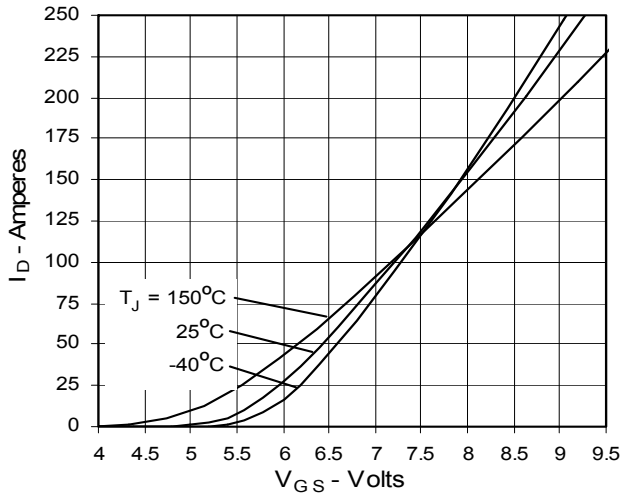
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Drain Current**



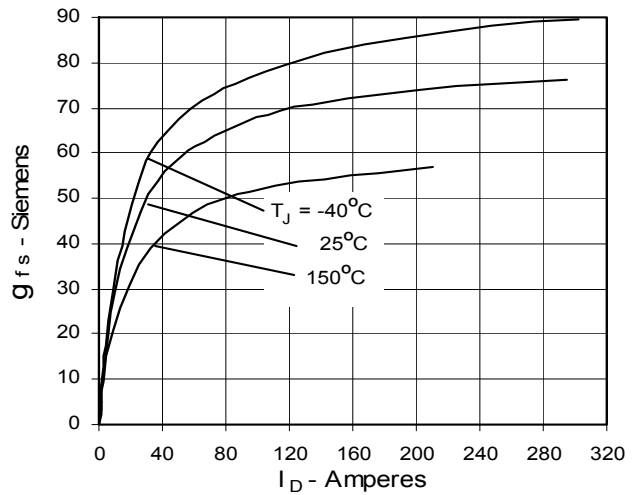
**Fig. 6. Drain Current vs. Case Temperature**



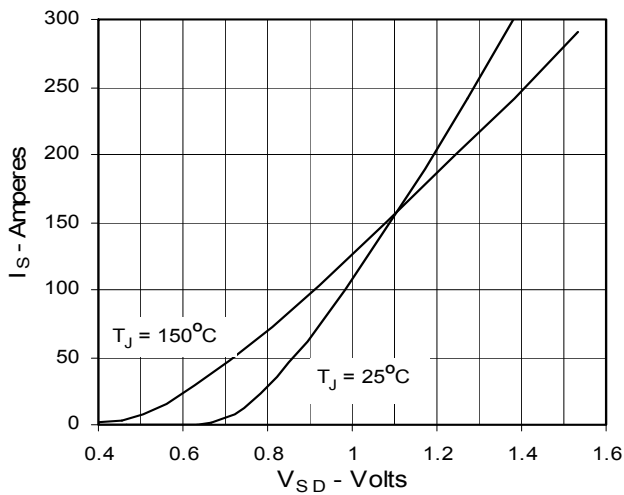
**Fig. 7. Input Admittance**



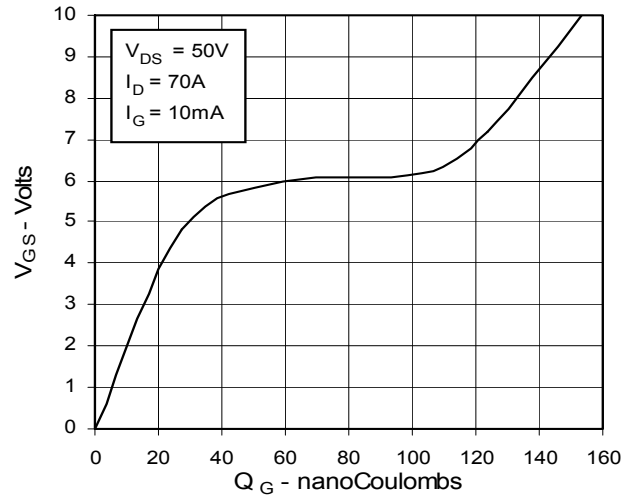
**Fig. 8. Transconductance**



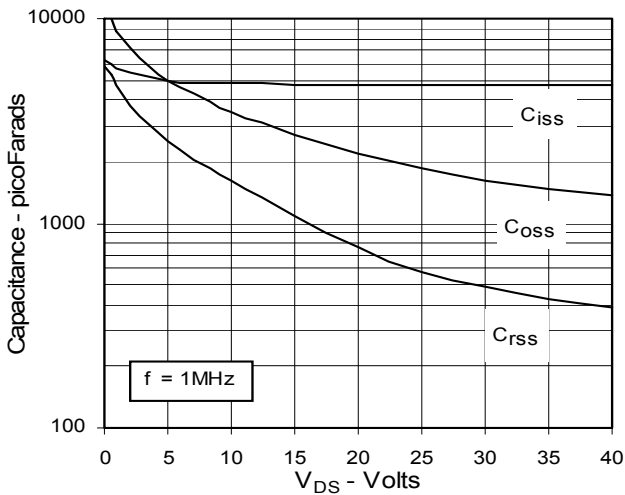
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

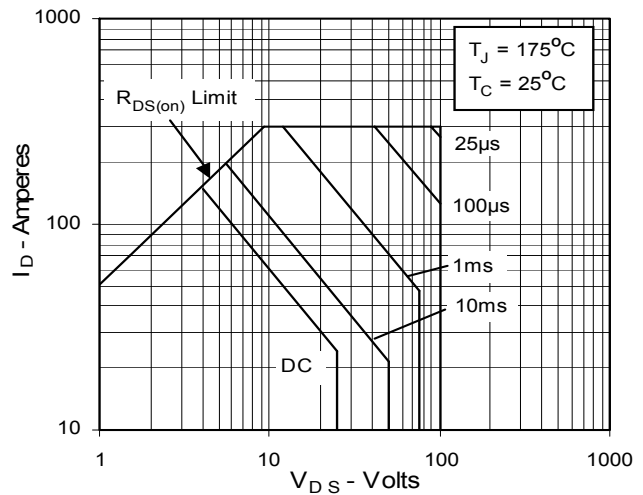
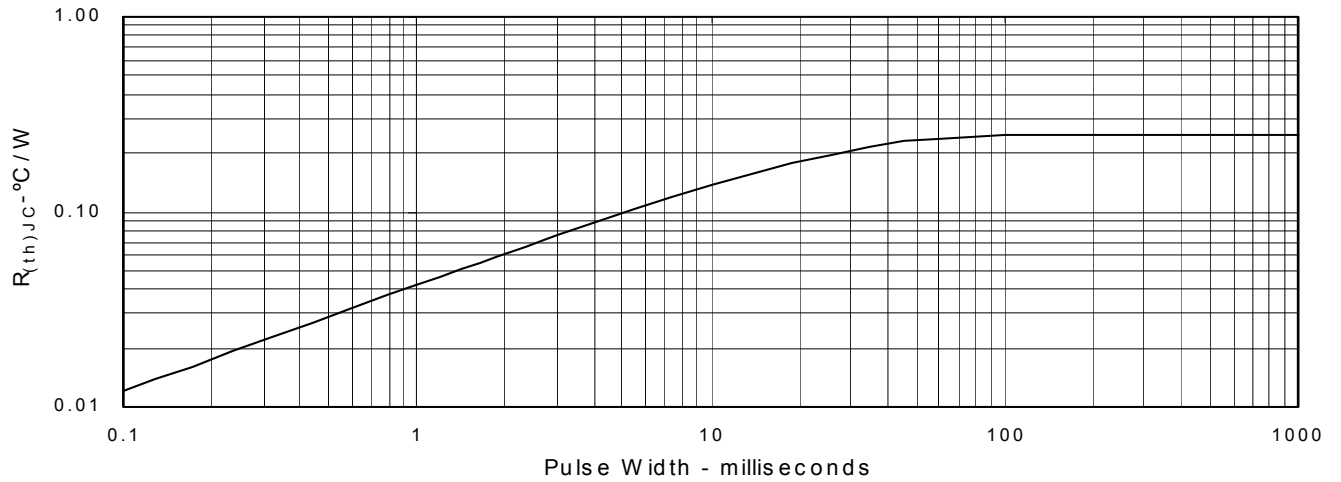


Fig. 13. Maximum Transient Thermal Resistance



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